



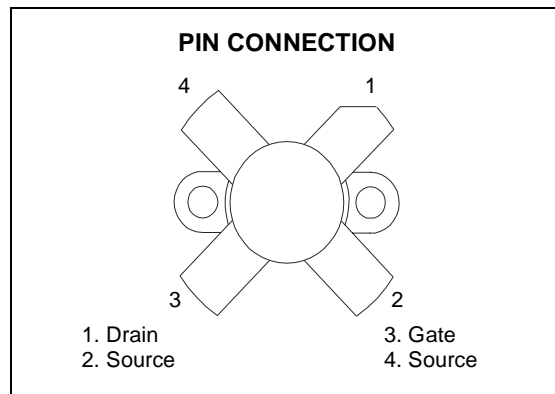
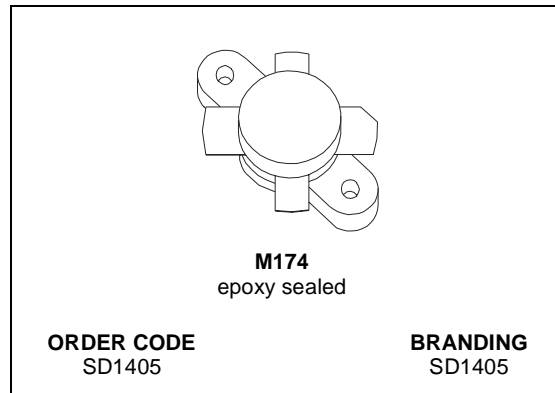
SD1405

RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

- 30 MHz
- 12.5 VOLTS
- COMMON EMITTER
- IMD 32 dB
- GOLD METALLIZATION
- $P_{OUT} = 75 \text{ W MIN. WITH } 13 \text{ dB GAIN}$

DESCRIPTION

The SD1405 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for HF communications. This device utilizes diffused emitter resistors to achieve infinite VSWR under rated operating conditions.



ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25 \text{ }^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	36	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	20	A
P_{DISS}	Power Dissipation	270	W
T_j	Max. Operating Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction -Case Thermal Resistance	0.65	$^{\circ}\text{C/W}$
---------------	-----------------------------------	------	----------------------

SD1405

ELECTRICAL SPECIFICATION ($T_{CASE} = 25^{\circ}C$)

STATIC

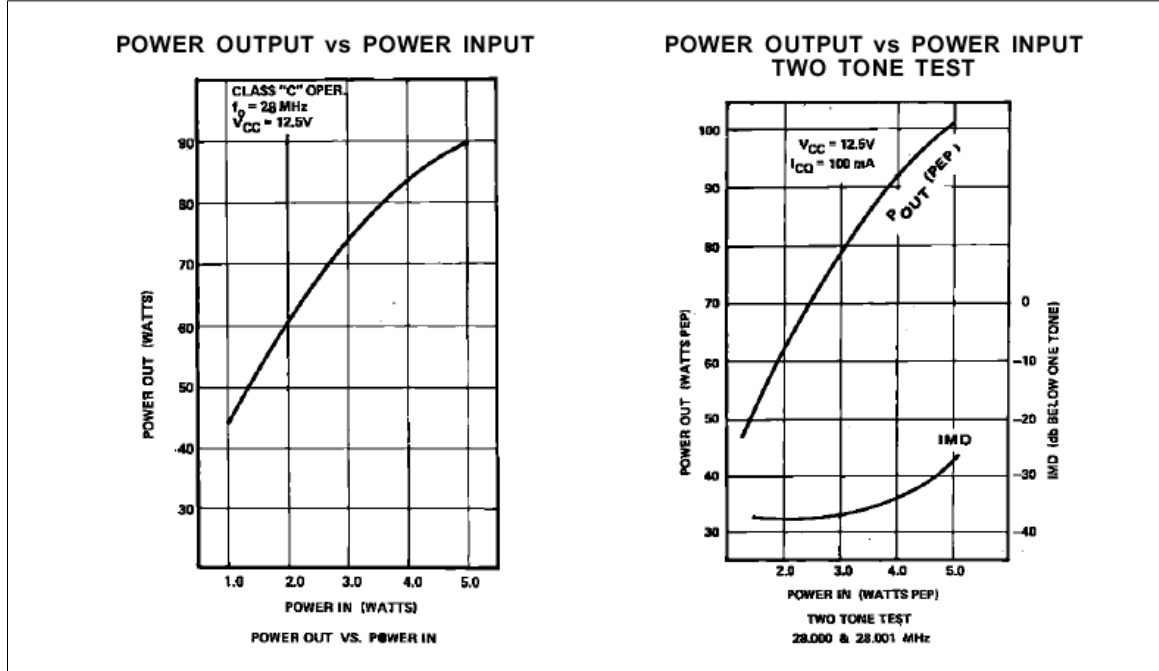
Symbol	Test Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	$I_C = 50\text{ mA}$ $I_E = 0\text{ mA}$	36			V
BV_{CES}	$I_C = 100\text{ mA}$ $V_{BE} = 0\text{ V}$	36			V
BV_{CEO}	$I_C = 100\text{ mA}$ $I_B = 0\text{ mA}$	18			V
BV_{EBO}	$I_E = 10\text{ mA}$ $I_C = 0\text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 15\text{ V}$ $I_E = 0\text{ mA}$			2	mA
h_{FE}	$V_{CE} = 5\text{ V}$ $I_C = 5\text{ A}$	20		300	

DYNAMIC

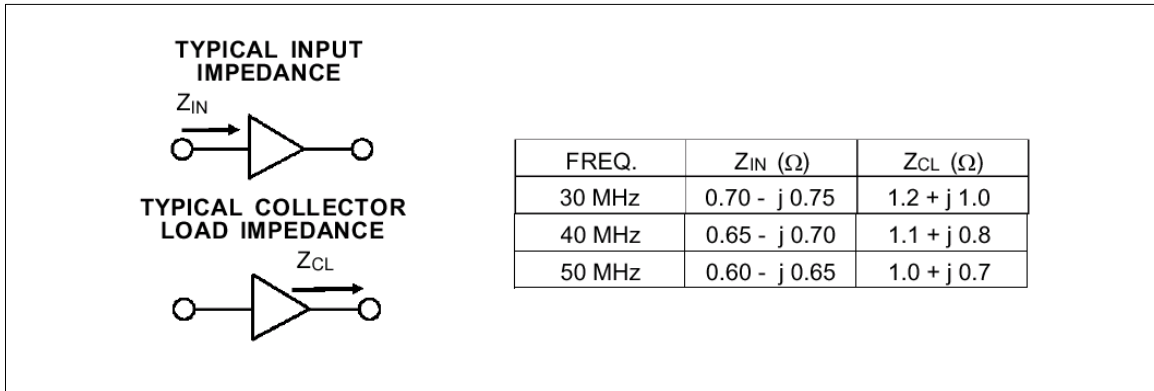
Symbol	Test Conditions	Min.	Typ.	Max.	Unit
P_{OUT}	$f = 30\text{ MHz}$ $P_{IN} = 3.8\text{ W}$ $V_{CE} = 12.5\text{ V}$	75			W
G_P	$f = 30\text{ MHz}$ $P_{IN} = 3.8\text{ W}$ $V_{CE} = 12.5\text{ V}$	13			dB
IMD*	$f = 30\text{ MHz}$ $V_{CE} = 12.5\text{ V}$ $I_{CQ} = 100\text{ mA}$	32			dB
C_{OB}	$f = 1\text{ MHz}$ $V_{CB} = 12\text{ V}$		350		pF

* $P_{OUT} = 60\text{ W PEP}$, $f_0 = 30 + 30.001\text{ MHz}$

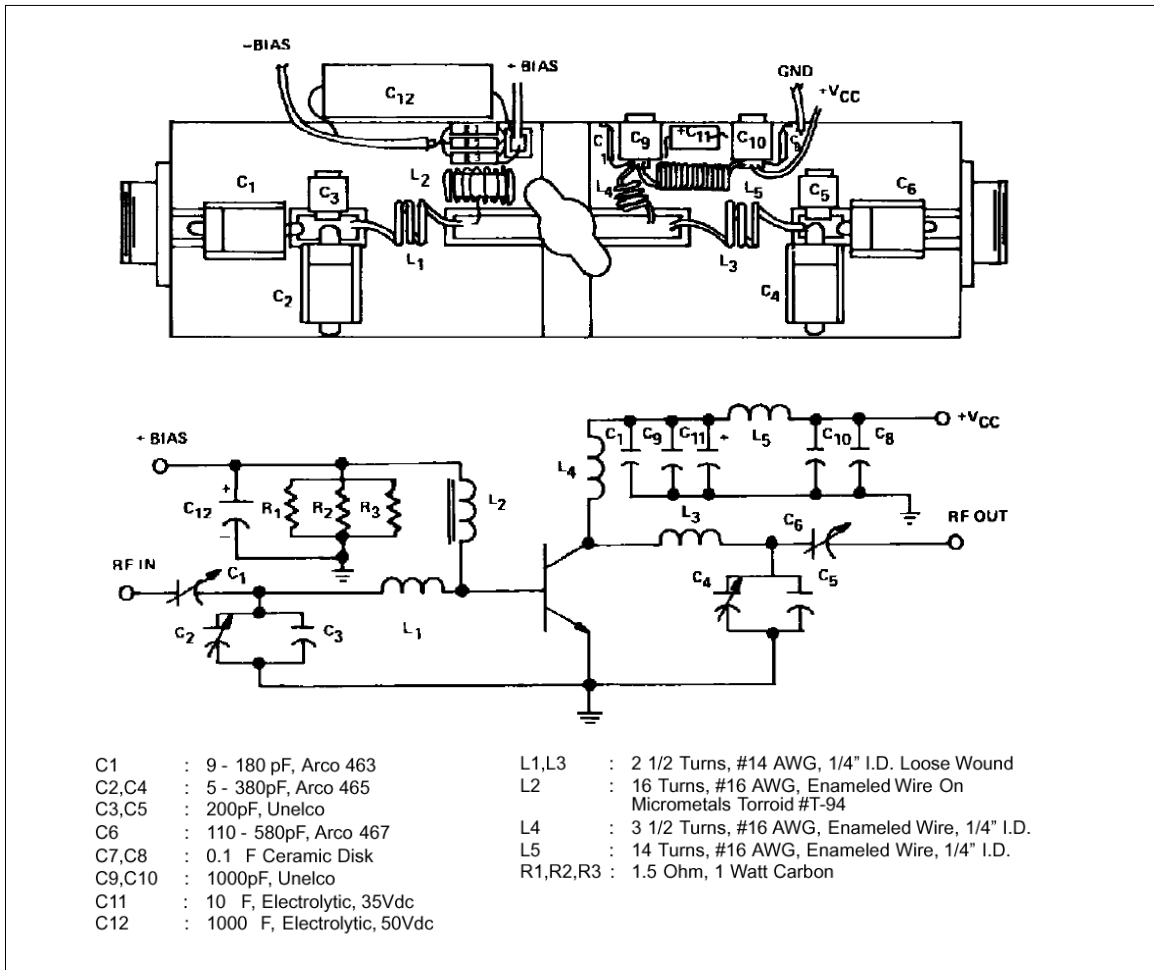
TYPICAL PERFORMANCE



IMPEDANCE DATA

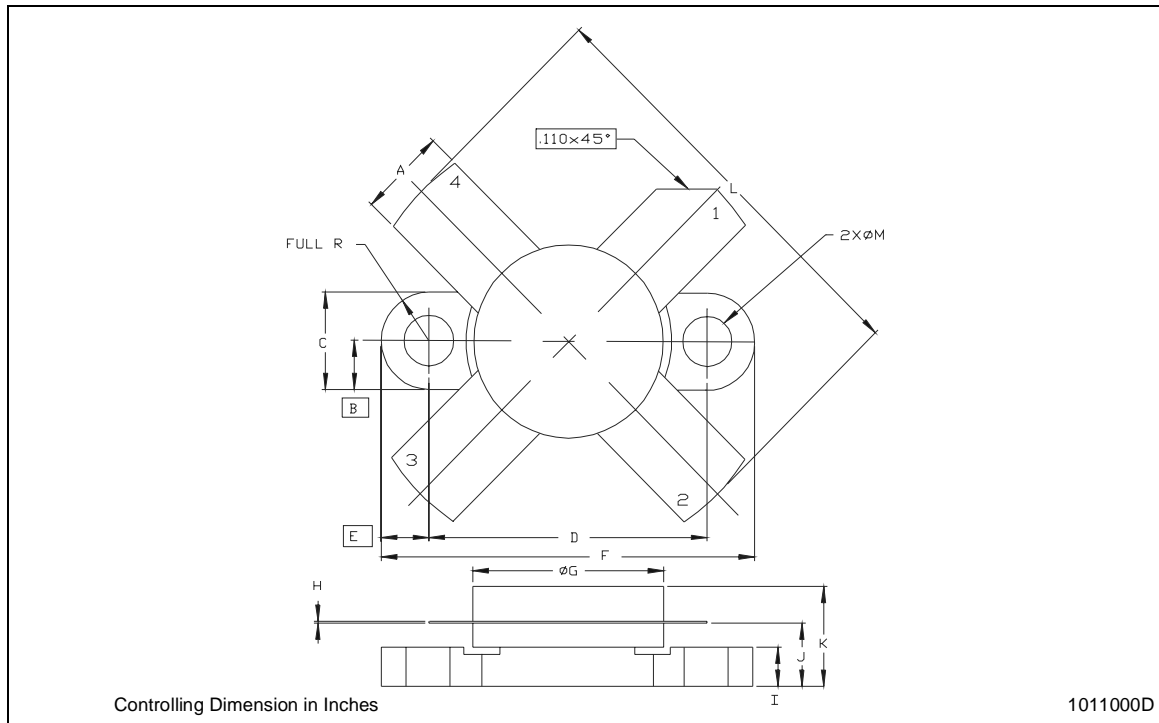


TEST CIRCUIT



M174 (.500 DIA 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	5.56		5.584	0.219		0.230
B		3.18			0.125	
C	6.22		6.48	0.245		0.255
D	18.28		18.54	0.720		0.730
E		3.18			0.125	
F	24.64		24.89	0.970		0.980
G	12.57		12.83	0.495		0.505
H	0.08		0.18	0.003		0.007
I	2.11		3.00	0.083		0.118
J	3.81		4.45	0.150		0.175
K			7.11			0.280
L	25.53		26.67	1.005		1.050
M	3.05		3.30	0.120		0.130



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics
® 2002 STMicroelectronics - All Rights Reserved

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>

